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Cypress Semiconductor
Product Qualification Report

QTP# 053301
June 2013

L8C-3R TECHNOLOGY, FAB 4	
CY5077	**3.3/3.0/2.5/1.8V High-Accuracy Programmable PLL Die for Crystal Oscillator**
CY22M1SxxLGX CY22M1LxxLGX	**MoBL(R) UniClock CY22M1 Single Output, Low Power Programmable Clock Generator for Portable Applications**
CY22U1SxxLGX CY22U1LxxLGX	**UniClock CY22U1 Single Output, Low Power Programmable Clock Generator**

CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

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Quality Engineering Director
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PRODUCT QUALIFICATION HISTORY

Qual Report	Description of Qualification Purpose	Date Comp
042106	7C82877A DDR2 PLL New Device family on New C8Q-3R Technology, Fab4	Jan 05
053301	Qualify L8C-3R Technology Derivative of the C8 Technology at Fab4 using CY5077 Device	Sep 06
063209	3 Layer Change to XO-LV Epson (CY5077) on L8C-3R Technology (Wafer Sales Only)	Sep 06
064904	8-Layer Improvement Change to XO LV Epson on L8C-3R Technology (Wafer Sales Only)	Mar 07
071303	1 Layer Yield Improvement Change to XO LV Epson on L8C-3R Technology (Wafer Sales Only)	May 07

PRODUCT DESCRIPTION (for qualification)	
Qualification Purpose: Qualify L8C-3R Technology Derivative of the C8 Technology at Fab4 using CY5077 Device	
Marketing Part #:	CY5077, CY22M1SxxLGX, CY22M1LxxLGX, CY22U1SxxLGX, CY22U1LxxLGX,
Device Description:	3.3/3.0/2.5/1.8V High-Accuracy Programmable PLL Die for Crystal Oscillators Single Output, Low Power Programmable Clock Generator for Portable Applications
Cypress Division:	Cypress Semiconductor Corporation – Consumer and Computation Division

TECHNOLOGY/FAB PROCESS DESCRIPTION			
Number of Metal Layers:	4	Metal Composition:	Metal 1: 100A Ti/3,200A Al 0.5% Cu /300A TiW Metal 2: 150A Ti/4,230A Al 0.5% Cu/300A TiW Metal 3: 150A Ti/4,230A Al 0.5% Cu/300A TiW Metal 4: 150A Ti/8,000A Al 0.5% Cu/300A TiW
Passivation Type and Materials:			1,000A TeOs / 9,000A Si_3N_4
Generic Process Technology/Design Rule (µ-drawn):			CMOS, 0.13 µm
Gate Oxide Material/Thickness (MOS):			SiO_2 DGOX 32/55A
Name/Location of Die Fab (prime) Facility:			CMI / Bloomington MN
Die Fab Line ID/Wafer Process ID:			Fab4, L8C-3R

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY SITE FACILITY
NONE	**Wafer Sales ONLY**

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	SZ08
Package Outline, Type, or Name:	8-Lead SOIC
Mold Compound Name/Manufacturer:	Nitto MP8500
Mold Compound Flammability Rating:	NA
Oxygen Rating Index:	NA
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	Ni-Pd-Au
Die Backside Preparation Method/Metallization:	Backgrind
Die Separation Method:	Saw Singulate
Die Attach Supplier:	Dexter
Die Attach Material:	QMI 509
Die Attach Method:	Epoxy
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au, 1.0mil
Thermal Resistance Theta JA °C/W:	193°C/W
Package Cross Section Yes/No:	N/A
Name/Location of Assembly (prime) facility:	CML-RA
MSL Level	3
Reflow Profile	260C

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	**CML-RA**

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENT

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Vcc Max=3.8V, 125°C Dynamic Operating Condition, Vcc Max=2.35V, 150°C	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc Max=3.8V, 125°C Dynamic Operating Condition, Vcc Max=2.35V, 150°C	P
Long Life Verification	Dynamic Operating Condition, Vcc Max=2.35V, 150°C	P
Low Temperature Operating Life	-30C, 4.3V	P
High Temperature Steady State life	125°C, 3.63V, Vcc Max	P
High Accelerated Saturation Test (HAST)	130°C, 3.63V, 85%RH Precondition: JESD22 Moisture Sensitivity Level 3 192 Hrs, 30C/60%RH+3IR-Reflow, 260°C+0, -5°C	P
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity Level 3 192 Hrs, 30C/60%RH+3IR-Reflow, 260°C+0, -5°C	P
Pressure Cooker	121°C, 100%RH, 15 Psig Precondition: JESD22 Moisture Sensitivity Level 3 192 Hrs, 30C/60%RH+3IR-Reflow, 260°C+0, -5°C	P
Electrostatic Discharge Human Body Model (ESD-HBM)	2200V MIL-STD-883, Method 3015.7	P
Electrostatic Discharge Human Body Model (ESD-HBM)	2200V JESD22, Method A114-B	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V JESD22-C101	P
Age Bond Strength	200C, 4hrs MIL-STD-883, Method 883-2011	P
Ball Shear	JESD22-B116A	P
Acoustic Microscopy	J-STD-020	P
Latch up Sensitivity	125C, ± 200mA/300mA In accordance with JEDEC 17	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal[3] A.F	Failure Rate
High Temperature Operating Life Early Failure Rate[1]	2,080 Devices	0	N/A	N/A	0 PPM
High Temperature Operating Life[1,2] Long Term Failure Rate	180,000 DHRs	0	0 .7	170	30 FIT

[1] Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.
[2] Chi-squared 60% estimations used to calculate the failure rate.
[3] Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp\left[\frac{E_A}{k}\left[\frac{1}{T_2} - \frac{1}{T_1}\right]\right]$$

where:

E_A =The Activation Energy of the defect mechanism.
k = Boltzmann's constant = 8.62×10^{-5} eV/Kelvin.
T_1 is the junction temperature of the device under stress and T_2 is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #: 042106

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL3							
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	COMP	17	0	
CY2SSTU877 (7C87741A)	4416666B	H20592	TAIWN-G	COMP	16	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	COMP	17	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	16	0	
STRESS: AGE BOND STRENGTH							
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	COMP	5	0	
CY68013A (7C682001A)	4416701	610437657	TAIWN-G	COMP	5	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	3	0	
STRESS: BALL SHEAR							
CY68013A (7C682001A)	4416701	610437657	TAIWN-G	COMP	5	0	
STRESS: DYNAMIC LATCH-UP TESTING (6.9V)							
CY68013A (7C682001A)	4416701	610437657	TAIWN-G	COMP	3	0	
STRESS: ESD-CHARGE DEVICE MODEL (500V)							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	COMP	9	0	
CY68013A (7C682000A)	4416666	610437102	TAIWN-G	COMP	9	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	COMP	9	0	
CY68013A (7C682000A)	4416701	610437702	TAIWN-G	COMP	9	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER JESD22, METHOD A114-B, 2200V							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	COMP	9	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	COMP	9	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	COMP	9	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2200V							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	COMP	3	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	COMP	3	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	COMP	3	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	3	0	

Reliability Test Data

QTP #: 042106

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP STEADY STATE LIFE TEST (150C, 3.63V)							
CY68013A (7C682005A)	4416701	610438121	TAIWN-G	80	80	0	
CY68013A (7C682005A)	4416701	610438121	TAIWN-G	168	80	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE (125C, 3.8V, Vcc Max)							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	96	499	0	
CY68013A (7C682005A)	4417143	610443845	TAIWN-G	96	514	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (125C, 3.8V, Vcc Max)							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	168	200	0	
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	1000	194	0	
CY68013A (7C682005A)	4417143	610443845	TAIWN-G	168	208	0	
CY68013A (7C682005A)	4417143	610443845	TAIWN-G	1000	208	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE (125C, 2.35V, Vcc Max)							
CY2SSTU877 (7C87741A)	4416666B	H20592	TAIWN-G	96	276	0	
CY2SSTU877 (7C82877A)	4416701	H20501	TAIWN-G	96	126	0	
CY2SSTU877 (7C87741A)	4416701	H20500	TAIWN-G	96	89	0	
CY2SSTU877 (7C87740A)	4416791B	H20536	TAIWN-G	96	169	0	
CY2SSTU877 (7C87741A)	4417975	H20583	TAIWN-G	96	304	0	
CY2SSTU877 (7C87741A)	4419587	H20650	TAIWN-G	96	500	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (125C, 3.8V, Vcc Max)							
CY2SSTU877 (7C87741A)	4416666B	H20592	TAIWN-G	1000	253	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	168	150	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	1000	150	0	
STRESS: HI-ACCEL SATURATION TEST (130C, 85%RH, 3.63V), PRE COND 192 HR, 30C/60%RH, MSL3							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	128	47	0	
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	256	47	0	
CY68013A (7C682000A)	4416701	610437702	TAIWN-G	128	47	0	
CY68013A (7C682000A)	4416701	610437702	TAIWN-G	256	45	0	
STRESS: HI-ACCEL SATURATION TEST (130C, 85%RH, 1.8V), PRE COND 192 HR, 30C/60%RH, MSL3							
CY2SSTU877 (7C87741A)	4417975	H20583	TAIWN-G	128	43	0	

Reliability Test Data

QTP #: 042106

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: LOW TEMPERATURE OPERATING LIFE (-30C, 4.3V)							
CY68013A (7C682005A)	4416701	*610438121*	TAIWN-G	500	80	0	
STRESS: STATIC LATCH-UP TESTING (125C, 5.5V, ±300mA)							
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	COMP	3	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 6.5V, ±300mA)							
CY68013A (7C682001A)	4416666	610437607	TAIWN-G	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 7.5V, ±300mA)							
CY68013A (7C682001A)	4416701	610437657	TAIWN-G	COMP	3	0	
STRESS: PRESSURE COOKER TEST (121C, 100%RH), 15 Psig, PRE COND 192 HR, 30C/60%RH, MSL3							
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	168	50	0	
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	288	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	168	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	288	50	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	168	47	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	288	47	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	168	45	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	288	45	0	
STRESS: TC COND. C -65C TO 150C, PRE COND 192 HRS, 30C/60%RH, MSL3							
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	300	50	0	
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	500	50	0	
CY68013A (7C681000A)	4416666	610434406	TAIWN-G	1000	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	168	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	500	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	1000	50	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	300	46	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	500	45	0	
CY2SSTU877 (7C82877A)	4413035	H19747	TAIWN-G	1000	45	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	300	45	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	500	45	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	1000	45	0	

Reliability Test Data

QTP #: 042106

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMPERATURE STORAGE, 150C, No bias							
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	500	50	0	
CY68013A (7C681000A)	4416701	610434407/8	TAIWN-G	1000	50	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	500	45	0	
CY2SSTU877 (7C87740A)	4417143	H20549	TAIWN-G	1000	45	0	

Reliability Test Data

QTP #: 053301

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL3							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	16	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	15	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	15	0	
STRESS: DYNAMIC LATCH-UP, 5.0V							
CY5077 (7C850003A)				COMP	2	0	
STRESS: DYNAMIC LATCH-UP, 6.25V							
CY5077 (7C850003A)				COMP	2	0	
STRESS: ESD-CHARGE DEVICE MODEL (500V)							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	9	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	9	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER JESD22, METHOD A114-B, 2200V							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	9	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	9	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	3	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2200V							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	3	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	3	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	3	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE (150C, 2.35V, Vcc Max)							
CY5077 (7C850003A)	4538565	610555083	CML-RA	48	519	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	48	1061	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	48	500	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST (150C, 2.35V)							
CY5077 (7C850003A)	4538565	610555083	CML-RA	80	79	0	
CY5077 (7C850003A)	4538565	610555083	CML-RA	168	79	0	

Reliability Test Data

QTP #: 053301

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE (150C, 2.35V, Vcc Max)							
CY5077 (7C850003A)	4538565	610555083	CML-RA	80	120	0	
CY5077 (7C850003A)	4538565	610555083	CML-RA	500	120	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	80	120	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	500	120	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	80	120	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	500	120	0	
STRESS: LONG LIFE VERIFICATION TEST (150C, 2.35V, Vcc Max)							
CY5077 (7C850003A)	4538565	610555083	CML-RA	1000	119	0	
STRESS: HI-ACCEL SATURATION TEST (130C, 85%RH, 2.35V), PRE COND 192 HR, 30C/60%RH, MSL3							
CY5077 (7C850003A)	4538565	610555083	CML-RA	128	48	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	128	48	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	256	47	0	
STRESS: HIGH TEMPERATURE STORAGE, 150C, no bias							
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	500	50	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	1000	50	0	
STRESS: STATIC LATCH-UP TESTING (125C, 3.0V, ±200mA), 1.8V Option							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	3	0	
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	3	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 6.5V, ±200mA), 3.3V Option							
CY5077 (7C850003A)	4538565	610555083	CML-RA	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 5.4V, ±200mA), 3.3V Option							
CY5077 (7C850003A)	4550443	61033232/3/915	PHIL-M	COMP	3	0	
CY5077 (7C850003A)	4615715	610637084	PHIL-M	COMP	3	0	

Reliability Test Data

QTP #: 053301

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: TC COND. C -65C TO 150C, PRE COND 192 HRS, 30C/60%RH, MSL3							
CY5077 (7C850003A)	4538565	*610555083*	CML-RA	300	50	0	
CY5077 (7C850003A)	4538565	*610555083*	CML-RA	500	50	0	
CY5077 (7C850003A)	4538565	*610555083*	CML-RA	1000	50	0	
CY5077 (7C850003A)	4550443	*61033232/3/915*	PHIL-M	300	50	0	
CY5077 (7C850003A)	4550443	*61033232/3/915*	PHIL-M	500	50	0	
CY5077 (7C850003A)	4550443	*61033232/3/915*	PHIL-M	1000	50	0	
CY5077 (7C850003A)	4615715	*610637084*	PHIL-M	300	49	0	
CY5077 (7C850003A)	4615715	*610637084*	PHIL-M	500	49	0	
CY5077 (7C850003A)	4615715	*610637084*	PHIL-M	1000	48	0	

Reliability Test Data

QTP #: 063209

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ESD-CHARGE DEVICE MODEL (500V)							
CY5077 (7C850003A)	4628387	*61065155/3*	PHIL-M	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER JESD22, METHOD A114-B, 2200V							
CY5077 (7C850003A)	4628387	*61065155/3*	PHIL-M	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2200V							
CY5077 (7C850003A)	4628387	*61065155/3*	PHIL-M	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 3.0V, ±200mA), 1.8V Option							
CY5077 (7C850003A)	4628387	61065155/3	PHIL-M	COMP	3	0	
STRESS: STATIC LATCH-UP TESTING (125C, 6.5V, ±200mA), 3.3V Option							
CY5077 (7C850003A)	4628387	61065155/3	PHIL-M	COMP	3	0	

Reliability Test Data

QTP #: 071303

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Results
STRESS: E-TEST YIELD					
CY5077 (7C850003A)	4644877			COMP	COMPARABLE
STRESS: SORT YIELD					
CY5077 (7C850003A)	4644877			COMP	COMPARABLE

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Document Number: 001-88090

Rev.	ECN No.	Orig. of Change	Description of Change
**	4039149	ILZ	Initial Spec Release Qualification report published on Cypress.com is documented on memo HGA-714 and not in spec format. Initiated spec for QTP 053301 and all data from memo# HGA-714 was transferred to qualification report spec template. Deleted package qualification details on package qualification history table. Deleted Cypress reference Spec and replaced with Industry Standards Updated package availability based on current qualified test & assembly site.

Distribution: WEB

Posting: None